# RT1N14BX SERIES

**(Transistor)** 

UNIT: mm

Transistor With Resistor For Switching Application Silicon NPN Epitaxial Type

## **DESCRIPTION**

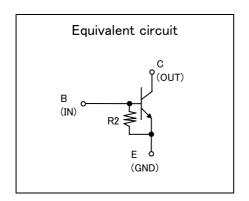
RT1N14BX is a one chip transistor with built-in bias resistor,PNP type is RT1P14BX.

### **FEATURE**

•Built-in bias resistor (R2=10k $\Omega$ ).

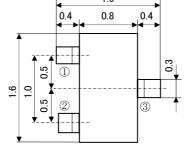
## **APPLICATION**

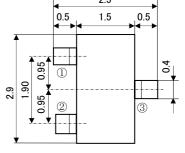
Inverted circuit, switching circuit, interface circuit, driver circuit.

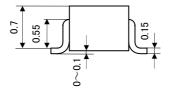


# RT1N14BU RT1N14BC 1.6 0.4 0.8 0.5 1.5 0.5

OUTLINE DRAWING









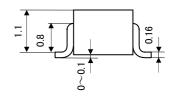
Terminal Connector

①:Base

2: Emitter

3: Collector

RT1N14BM



JEITA: SC-59

JEDEC: Similar to TO-236

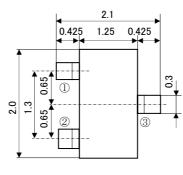
Terminal Connector

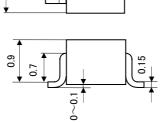
①:Base

2: Emitter

3: Collector

RT1N14BS





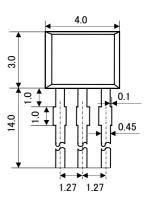
JEITA:SC-70 JEDEC:—

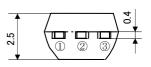
Terminal Connector

1:Base

2: Emitter

3: Collector





JEITA: — JEDEC: —

Terminal Connector

①:Emitter

2: Collector

3:Base

## **(Transistor)**

# RT1N14BX SERIES

Transistor With Resistor
For Switching Application
Silicon NPN Epitaxial Type

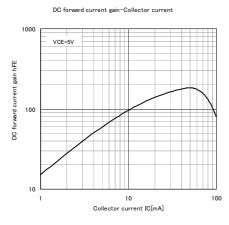
## MAXIMUM RATING (Ta=25°C)

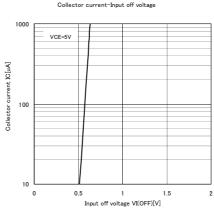
SYMBOL	PARAMETER	RATING				UNIT
		RT1N14BU	RT1N14BM	RT1N14BC	RT1N14BS	OINII
V <sub>CBO</sub>	Collector to Base voltage	50				
$V_{EBO}$	Emitter to Base voltage	6				
$V_{CEO}$	Collector to Emitter voltage	50				
Ic	Collector current	100				
I <sub>CM</sub>	Peak Collector current	200				
Pc	Collector dissipation(Ta=25°C)	150	20	00	450	mW
Tj	Junction temperature	+150	+150			°C
Tstg	Storage temperature	−55 <b>~</b> +150	−55 <b>~</b> +150			°C

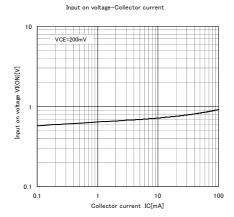
## ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
		TEST CONDITION	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	C to E break down voltage	I <sub>C</sub> =100 μ A, R <sub>BE</sub> =∞	50			٧
I <sub>CBO</sub>	Collector cut off current	$V_{CB}$ =50V, I $_{E}$ =0			0.1	μΑ
h <sub>FE</sub>	DC forward current gain	$V_{CE}$ =5V, I $_{C}$ =5mA	30			-
$V_{CE(sat)}$	C to E saturation voltage	$I_{\rm C}$ =10mA, $I_{\rm B}$ =0.5mA			0.3	٧
R <sub>2</sub>	Emitter-base resistance		7	10	13	kΩ
f⊤	Gain band width product	$V_{CE}=6V$ , $I_{E}=-10mA$		200		MHz

## TYPICAL CHARACTERISTICS









Marketing division, Marketing planning department 6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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